High-voltage Switching Transistor (Telephone power supply) (-400V, -0.5A) 2SA1812 / 2SA1727 / 2SA1776

- 1) High breakdown voltage, BVcEo=-400V.
- 2) Low saturation voltage, typically $V_{CE(sat)} = -0.3V$ at Ic / I_B= -100mA / -10mA.
- 3) High switching speed, typically tf=1 μ s at Ic=-100mA.
- 4) Wide SOA (safe operating area).

Packaging specifications and hre

Туре	2SA1812	2SA1727	2SA1776	
Package	MPT3	CPT3	ATV	
hre	PQ	PQ	PQ	
Marking	AJ*	_	_	
Code	T100	TL	TV2	
Basic ordering unit (pieces)	3000	3000	2500	

^{*} Denotes hre

●Absolute maximum ratings (Ta=25℃)

Parameter		Symbol	Limits	Unit	
Collector-base voltage		Vсво	-400	V	
Collector-emitter voltage		Vceo	-400	V	
Emitter-base voltage		VEBO	-7 V		
Callector current			-0.5 A (DC)		
		lc	-1.0	A (Pulse)	*1
Collector power dissipation	2\$A1812	-	0.5 W		
			2	W	*2
	2SA1727	Pc	1	W	
			10	W(Tc=25°C)	
	2\$A1776	1	1	W	*3
Junction tempera	ture	Tj	150	°C	
Storage temperature		Tstg	-55~+150	°C	

^{*1} Single pulse *2 When mounted on a 40×40×0.7mm ceramic board.

●Electrical characteristics (Ta=25℃)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	-400	_	_	V	Ic=-50 μ A	
Collector-emitter breakdown voltage	BVceo	-400	_	_	V	Ic=-1mA	
Emitter-base breakdown voltage	BVEBO	-7	_	_	V	I _E =-50 μ A	
Collector cutoff current	Ісво	_	_	-1	μΑ	VcB=-400V	
Emitter cutoff current	Ієво	_	_	-1	μА	V _{EB} =-6V	
DC current transfer ratio	hre	82	150	270	_	Vc=-5V, Ic=-50mA	
Collector-emitter saturation voltage	VCE(sat)	_	_	-1	V	Ic/I _B =-100mA/-10mA	
Base-emitter saturation voltage	VBE(sat)	_	_	-1.2	V	Ic/I _B =-100mA/-10mA	
Transition frequency	fτ	_	12	_	MHz	VcB=-5V, IE=50mA, f=5MHz	
Output capacitance	Cob	_	18	_	pF	Vc=-10V , IE=0A , f=1MHz	
Turn-on time	ton	_	0.6	_	μS	$l_{c}=-100\text{mA}$, $R_{L}=1.5k\Omega$ $l_{B1}=-l_{B2}=-10\text{mA}$ $V_{CC}\underline{\sim}-150V$	
Storage time	tstg	_	2.7	_	μs		
Fall time	tı	_	1	_	μs		

(96-609-A313)

^{*3} When t = 1.7mm and the foil collector area on the PC board is 1cm² or greater.